

Amendments to the Claims:

Claims 1-25 (Canceled).

26. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall; a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing; and

a chamber liner apparatus forming a deposition subchamber within the chamber, at least a portion of the chamber liner apparatus being selectively movable to fully expose the passageway to the chamber and to fully cover and seal the passageway from the chamber and to form a gas-tight seal between the passageway and the chamber.

27. (Original): The apparatus of claim 26 further comprising a movable substrate holder received within the subchamber, the portion of the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

28. (Original): The apparatus of claim 26 further comprising a movable substrate holder received within the subchamber, the portion of the chamber liner apparatus being mounted for movement with movement of the substrate holder.

29. (Original): The apparatus of claim 26 wherein the portion is mounted for elevational movement, upward movement of the portion to a first position fully exposing the passageway, downward movement of the portion to a second position fully covering the passageway.

30. (Original): The apparatus of claim 26 wherein the portion is mounted for elevational movement, upward movement of the portion to a first position fully covering the passageway, downward movement of the portion to a second position fully exposing the passageway.

31. (Original): The apparatus of claim 26 wherein an entirety of the liner apparatus is selectively movable to fully expose and to fully cover the passageway to the chamber

32. (Original): The apparatus of claim 26 wherein only a portion of the liner apparatus is selectively movable to fully expose and to fully cover the passageway to the chamber, another portion of the liner apparatus not being mounted for movement.

33. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall;

a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing; and

a movable chamber liner apparatus forming a deposition subchamber within the chamber, the liner apparatus having a substrate opening therethrough, the liner apparatus being mounted for movement to a first position in which the opening is aligned with the passageway and to a second position in which the opening is not aligned with the passageway, ~~the passageway~~, the second position fully covering ~~and sealing~~ the passageway from the chamber with the liner apparatus and forming a gas-tight seal between the passageway and the chamber.

Claims 34 and 35 (Canceled).

36. (Original): The apparatus of claim 33 wherein the passageway has a total open cross section where it joins with the chamber, the opening being at least as large as said cross section.

37. (Original): The apparatus of claim 33 wherein the passageway has a total open cross section where it joins with the chamber, the opening having a shape the same as that of said cross section.

38. (Original): The apparatus of claim 33 wherein the passageway has a total open cross section where it joins with the chamber, the opening having a size and shape the same as that of said cross section.

39. (Original): The apparatus of claim 33 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

40. (Original): The apparatus of claim 33 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement with movement of the substrate holder.

41. (Original): The apparatus of claim 33 wherein the liner apparatus is mounted for elevational movement, upward movement of the liner apparatus to the first position fully exposing the passageway, downward movement of the liner apparatus to the second position fully covering the passageway.

42. (Original): The apparatus of claim 33 wherein the liner apparatus is mounted for elevational movement, upward movement of the liner apparatus to the second position fully covering the passageway, downward movement of the liner apparatus to the first position fully exposing the passageway.

43. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall;

a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing, the passageway having a total open cross section where it joins with the chamber; and

a movable chamber liner apparatus forming a deposition subchamber within the chamber, the liner apparatus having a substrate opening therethrough, the opening being at least as large as said total open cross section of the passageway, the liner apparatus being mounted for elevational movement to a first position in which the opening is aligned with the passageway and to a second position in which the opening is not aligned with the passageway, the second position fully covering ~~and sealing~~ the passageway from the chamber with the liner apparatus and forming a gas-tight seal between the passageway and the chamber.

Claims 44 and 45 (Cancelled).

46. (Original): The apparatus of claim 43 wherein the passageway has a total open cross section where it joins with the chamber, the opening having a shape the same as that of said cross section.

47. (Original): The apparatus of claim 43 wherein the passageway has a total open cross section where it joins with the chamber, the opening having a size and shape the same as that of said cross section.

48. (Original): The apparatus of claim 43 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

49. (Original): The apparatus of claim 43 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement with movement of the substrate holder.

50. (Currently Amended): The apparatus of claim 26 wherein said portion of the chamber liner apparatus comprises opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces.

51. (Currently Amended): The apparatus of claim 33 wherein the chamber liner apparatus comprises opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces, the substrate opening being received in one of the opposing sidewall sections, the base being movable with the sidewall sections.

52. (Currently Amended): The apparatus of claim 43 wherein the chamber liner apparatus comprises opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces, the substrate opening being received in one of the opposing sidewall sections, the base being movable with the sidewall sections.

53. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall;

a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing; and

a chamber liner apparatus forming a deposition subchamber within the chamber, at least a portion of the chamber liner apparatus comprising opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces, said portion including the opposing sidewall sections and the base being selectively movable to fully expose and to fully cover the passageway to the chamber.

54. (Previously Presented): The apparatus of claim 53 further comprising a movable substrate holder received within the subchamber, the portion of the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

55. (Previously Presented): The apparatus of claim 53 further comprising a movable substrate holder received within the subchamber, the portion of the chamber liner apparatus being mounted for movement with movement of the substrate holder.

56. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall;

a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing; and

a movable chamber liner apparatus forming a deposition subchamber within the chamber, the liner apparatus having opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces, one of the opposing sidewall sections comprising a substrate opening therethrough, the liner apparatus with opposing sidewall sections and the base being mounted for movement to a first position in which the opening is aligned with the passageway and to a second position in which the opening is not aligned with the passageway.

57. (Previously Presented): The apparatus of claim 56 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

58. (Previously Presented): The apparatus of claim 56 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement with movement of the substrate holder.

59. (Currently Amended): A chemical vapor deposition apparatus comprising:

a chamber defined at least in part by a chamber sidewall;

a passageway in the chamber sidewall extending from externally of the chamber to the chamber, and through which semiconductor substrates pass into and out of the chamber for deposition processing, the passageway having a total open cross section where it joins with the chamber; and

a movable chamber liner apparatus forming a deposition subchamber within the chamber, the liner apparatus having opposing sidewall sections having inner faces and a base extending from and received between the opposing sidewall sections inner faces, one of the opposing sidewall sections comprising a substrate opening therethrough, the opening being at least as large as said total open cross section of the passageway, the liner apparatus with opposing sidewall sections and the base being mounted for elevational movement to a first position in which the opening is aligned with the passageway and to a second position in which the opening is not aligned with the passageway.

60. (Previously Presented): The apparatus of claim 59 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement independent of movement of the substrate holder.

61. (Previously Presented): The apparatus of claim 59 further comprising a movable substrate holder received within the subchamber, the chamber liner apparatus being mounted for movement with movement of the substrate holder.